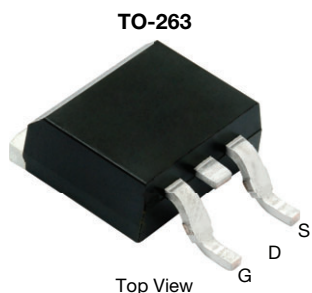


Automotive P-Channel 40 V (D-S) 175 °C MOSFET

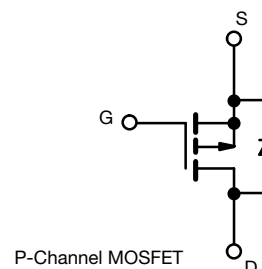


FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_g and UIS tested
- AEC-Q101 qualified
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE



PRODUCT SUMMARY	
V_{DS} (V)	-40
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	0.0034
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.0048
I_D (A)	-120
Configuration	Single
Package	TO-263

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-40	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current	$T_C = 25$ °C ^a	I_D	-120	A
	$T_C = 125$ °C		-90	
Continuous source current (diode conduction) ^a		I_S	-120	
Pulsed drain current ^b		I_{DM}	-315	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	-51	
		E_{AS}	130	mJ
Maximum power dissipation ^b	$T_C = 25$ °C	P_D	157	W
	$T_C = 125$ °C		52	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R_{thJA}	40	°C/W
Junction-to-case (drain)		R_{thJC}	0.95	

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)

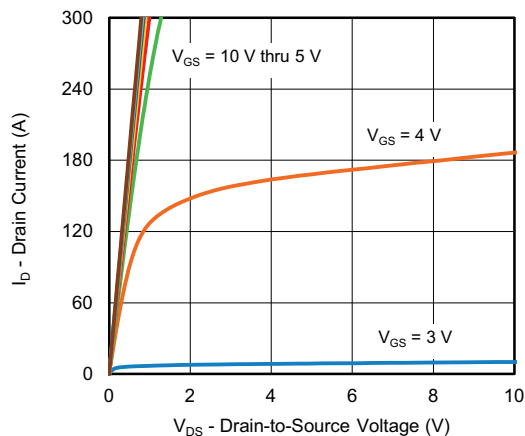
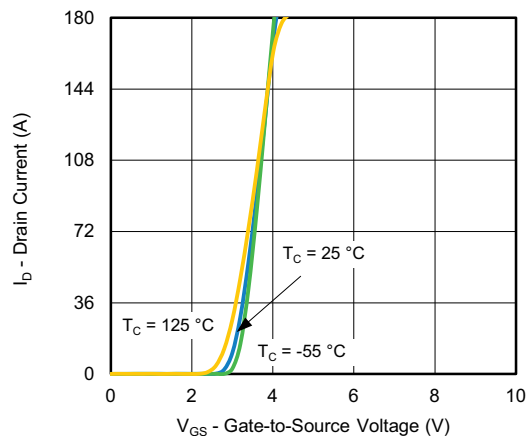
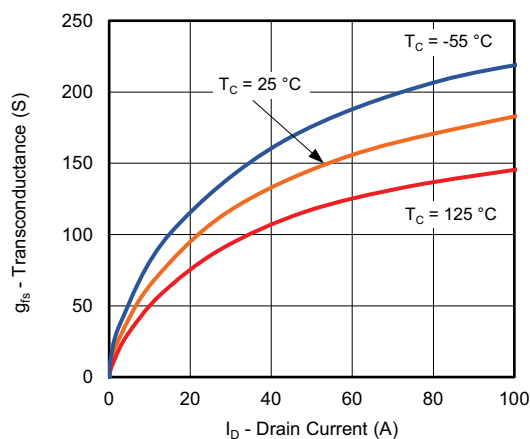
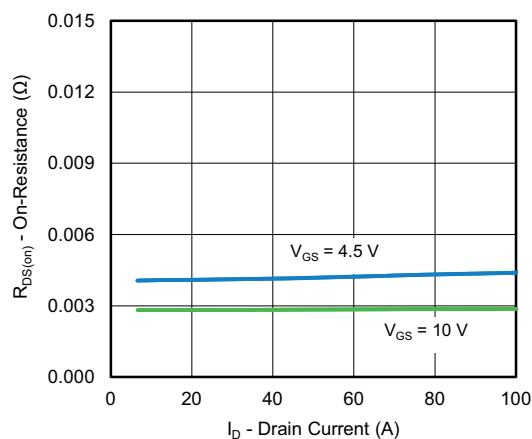
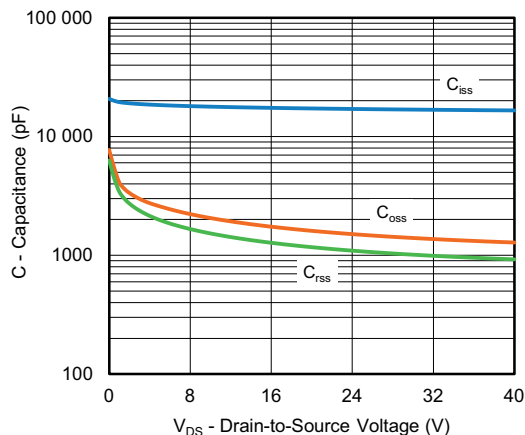
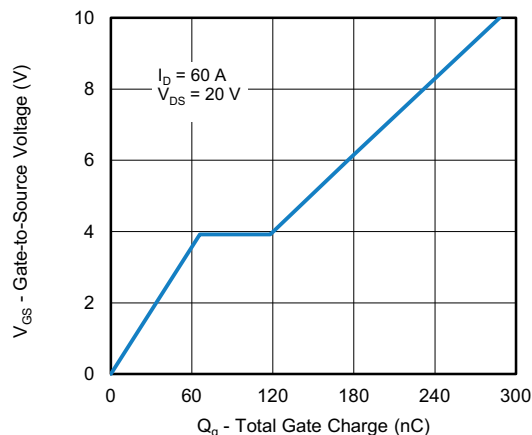


SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA		-1.5	-	-2.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -40 V	-	-	-1	μA
		V _{GS} = 0 V	V _{DS} = -40 V, T _J = 125 °C	-	-	-50	
		V _{GS} = 0 V	V _{DS} = -40 V, T _J = 175 °C	-	-	-250	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≤ -5 V	-50	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -25 A	-	0.00283	0.00340	Ω
		V _{GS} = -10 V	I _D = -25 A, T _J = 125 °C	-	-	0.00520	
		V _{GS} = -10 V	I _D = -25 A, T _J = 175 °C	-	-	0.00620	
		V _{GS} = -4.5 V	I _D = -20 A	-	0.00400	0.00480	
Forward transconductance ^a	g _{fs}	V _{DS} = -15 V, I _D = -25 A		-	92	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = -25 V, f = 1 MHz	-	17 027	23 600	pF
Output capacitance	C _{oss}			-	1487	2100	
Reverse transfer capacitance	C _{rss}			-	1079	1500	
Total gate charge ^c	Q _g	V _{GS} = -10 V	V _{DS} = -20 V, I _D = -60 A	-	288	450	nC
Gate-source charge ^c	Q _{gs}			-	66	-	
Gate-drain charge ^c	Q _{gd}			-	52	-	
Gate resistance	R _g	f = 1 MHz		1.3	2.65	4	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = -20 V, R _L = 0.33 Ω I _D ≅ -60 A, V _{GEN} = -10 V, R _g = 1 Ω		-	18	30	ns
Rise time ^c	t _r			-	20	40	
Turn-off delay time ^c	t _{d(off)}			-	155	300	
Fall time ^c	t _f			-	135	250	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	-315	A
Forward voltage	V _{SD}	I _F = -50 A, V _{GS} = 0 V		-	-0.85	-1.5	V
Body diode reverse recovery time	t _{rr}	I _F = -50 A, di/dt = 100 A/μs		-	33	70	ns
Body diode reverse recovery charge	Q _{rr}			-	29	60	nC
Reverse recovery fall time	t _a			-	18	-	ns
Reverse recovery rise time	t _b			-	15	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.7	-	A

Notes

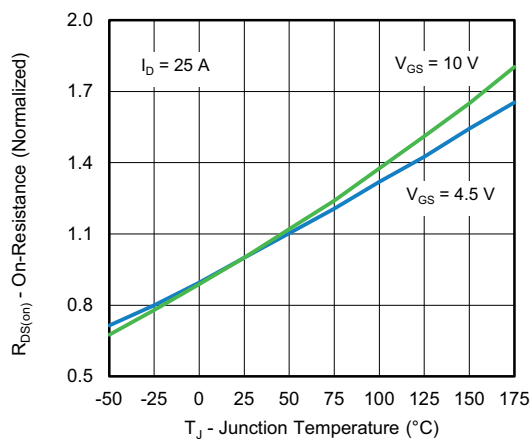
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

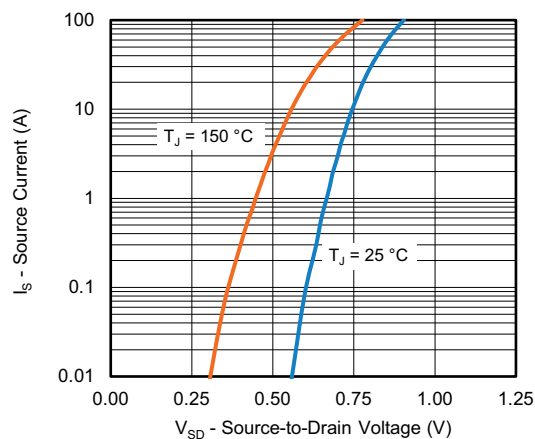
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge



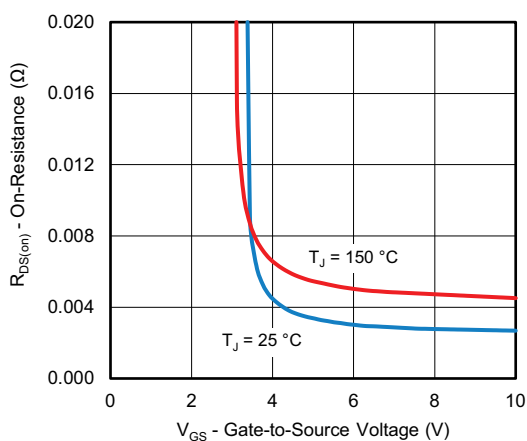
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



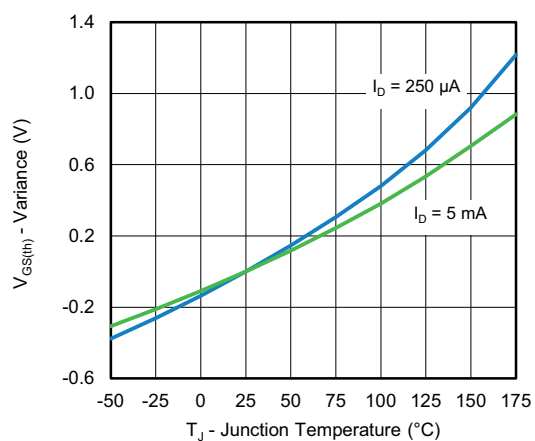
On-Resistance vs. Junction Temperature



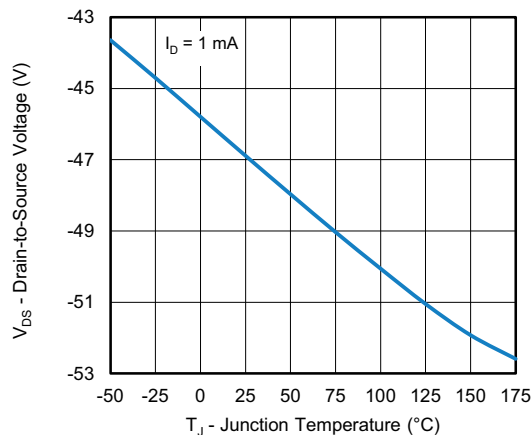
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



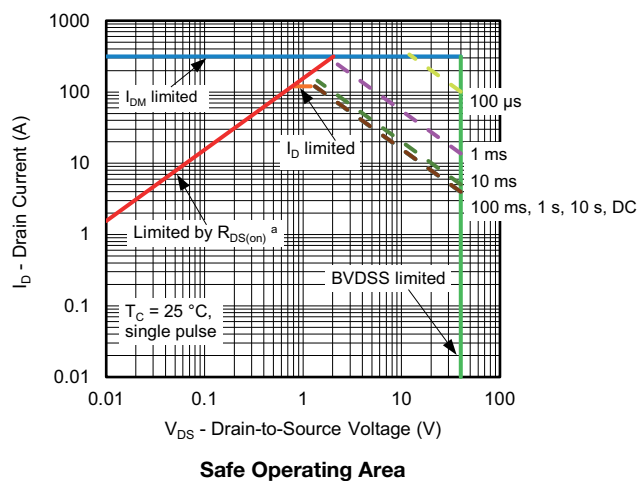
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

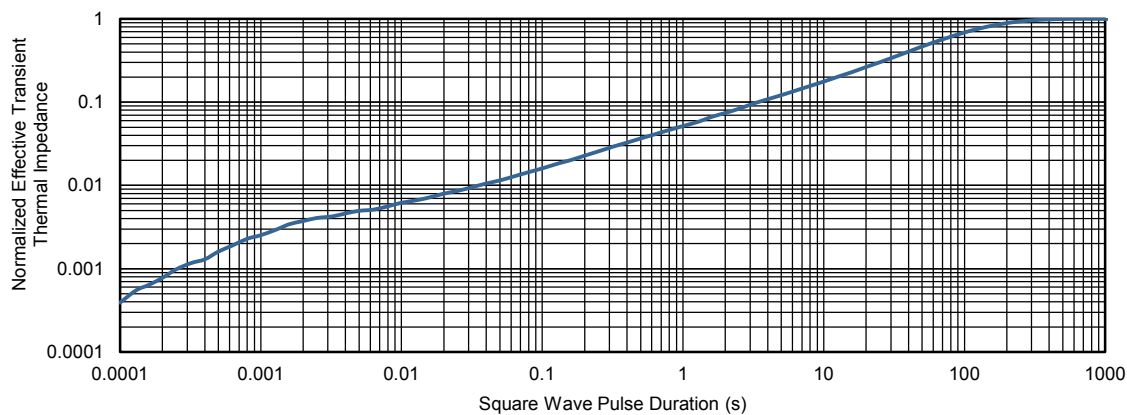


THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Note

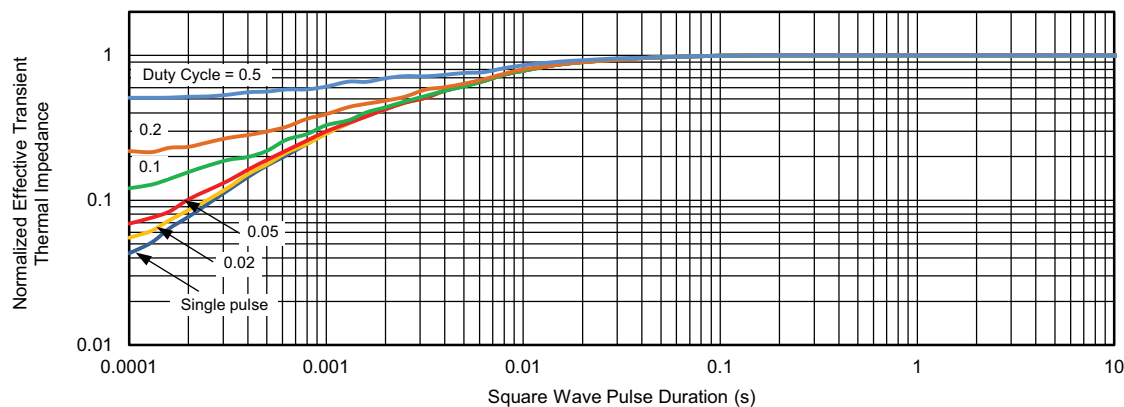
a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

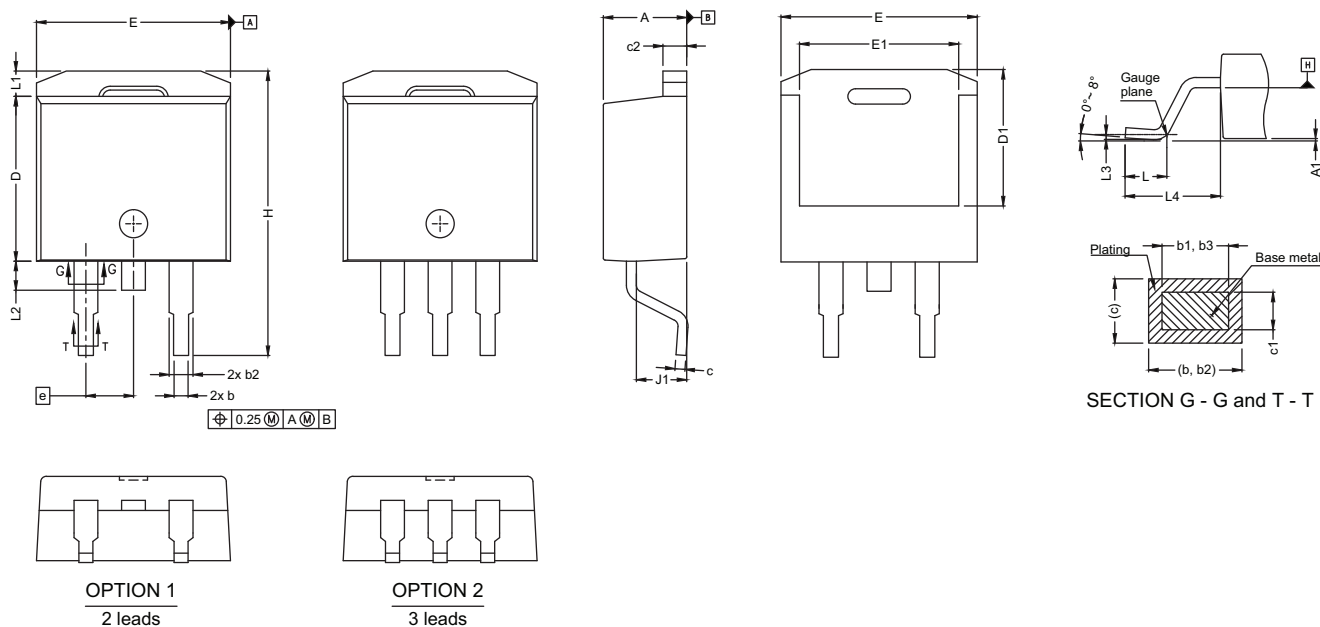


Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^{\circ}\text{C}$)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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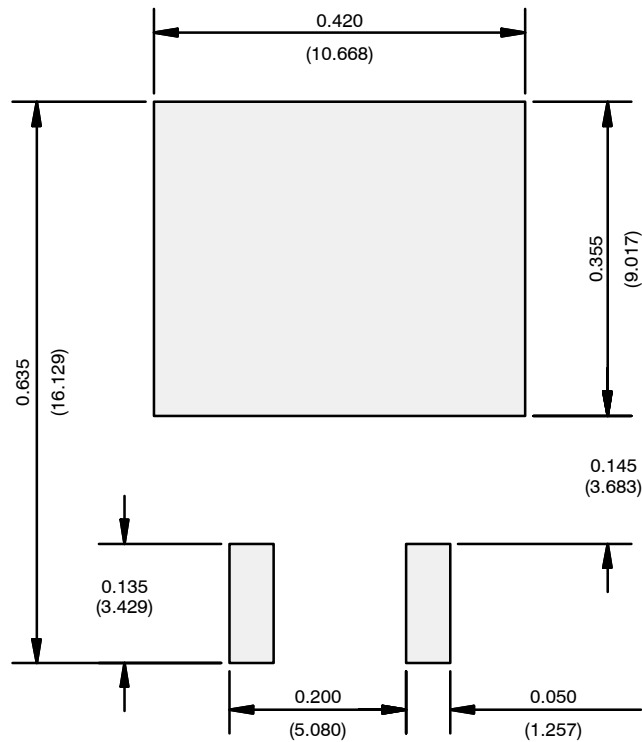
VERSION 2: FACILITY CODE = N

DIM.	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.70	0.90
b1	0.51	0.89
b2	1.20	1.46
b3	1.17	1.37
c	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.60	9.00
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
e	2.54 BSC	
H	15.0	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25 typ.	
L4	4.78	5.28
J1	2.56	2.96

ECN: S24-1080-Rev. L, 28-Oct-2024

DWG: 5843

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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